

NTST30100CT, NTSB30100CT-1G, NTSJ30100CTG, NTSB30100CTG



ON Semiconductor®

<http://onsemi.com>

Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.455\text{ V}$ at $I_F = 5\text{ A}$

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- Pb-Free and Halide-Free Packages are Available

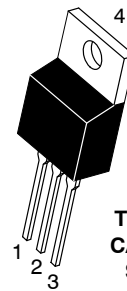
Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

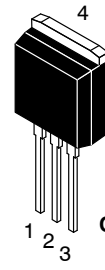
Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

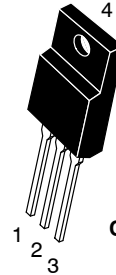
PIN CONNECTIONS



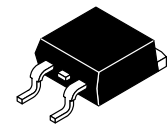
TO-220AB
CASE 221A
STYLE 6



I2PAK
CASE 418D
STYLE 3



TO-220FP
CASE 221AH



D2PAK
CASE 418B

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTST30100CT, NTSB30100CT-1G, NTSJ30100CTG, NTSB30100CTG

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|---------------------------------|-------------|------------------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V_{RRM} V_{RWM} V_R | 100 | V |
| Average Rectified Forward Current (Rated V_R , $T_C = 115^\circ\text{C}$) | $I_{F(AV)}$ | 30 15 | A |
| Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz, $T_C = 110^\circ\text{C}$) | I_{FRM} | 60 30 | A |
| Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz) | I_{FSM} | 160 | A |
| Operating Junction Temperature | T_J | -40 to +150 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | -40 to +150 | $^\circ\text{C}$ |
| Voltage Rate of Change (Rated V_R) | dv/dt | 10,000 | V/ μs |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

| Rating | Symbol | NTST30100CTG, NTSB30100CT-1G | NTSB30100CTG | NTSJ30100CTG | Unit |
|---|------------------------------------|---------------------------------|--------------|--------------|--|
| Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient | $R_{\theta JC}$ $R_{\theta JA}$ | 2.5 70 | 1.14 46.6 | 4.09 105 | $^\circ\text{C}/\text{W}$ $^\circ\text{C}/\text{W}$ |

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

| Rating | Symbol | Typ | Max | Unit |
|---|--------|--|--------------------------------------|--|
| Maximum Instantaneous Forward Voltage (Note 1) ($I_F = 5\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 7.5\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 15\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 5\text{ A}$, $T_J = 125^\circ\text{C}$) ($I_F = 7.5\text{ A}$, $T_J = 125^\circ\text{C}$) ($I_F = 15\text{ A}$, $T_J = 125^\circ\text{C}$) | V_F | 0.516 0.576 0.734 0.455 0.522 0.627 | - - 0.85 - - 0.68 | V |
| Maximum Instantaneous Reverse Current (Note 1) ($V_R = 70\text{ V}$, $T_J = 25^\circ\text{C}$) ($V_R = 70\text{ V}$, $T_J = 125^\circ\text{C}$) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 125^\circ\text{C}$) | I_R | 7.2 8.0 65 20 | 500 35 | μA mA μA mA |

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$

TYPICAL CHARACTERISTICS

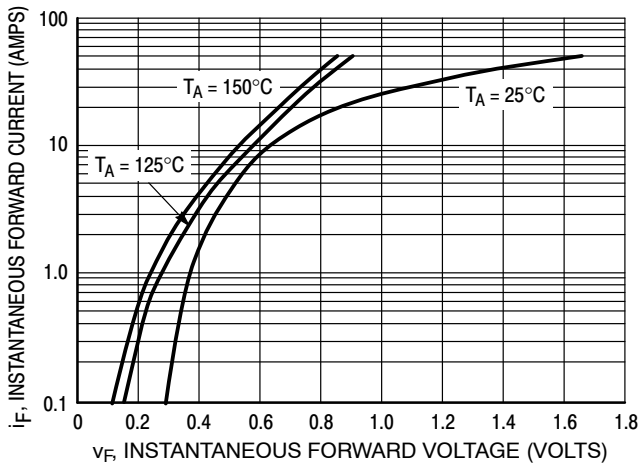


Figure 1. Typical Forward Voltage

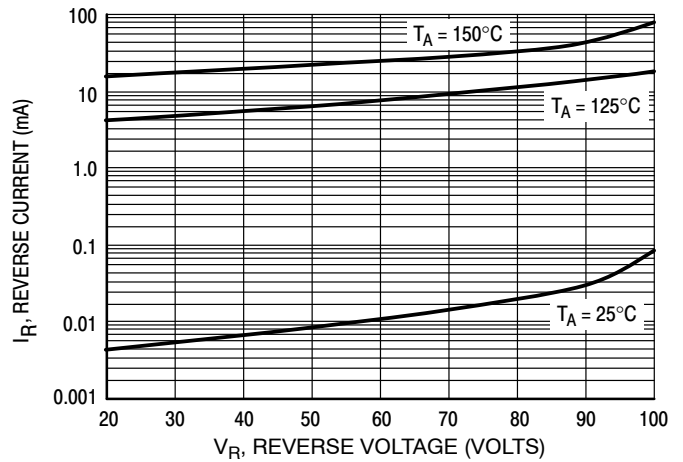


Figure 2. Typical Reverse Current

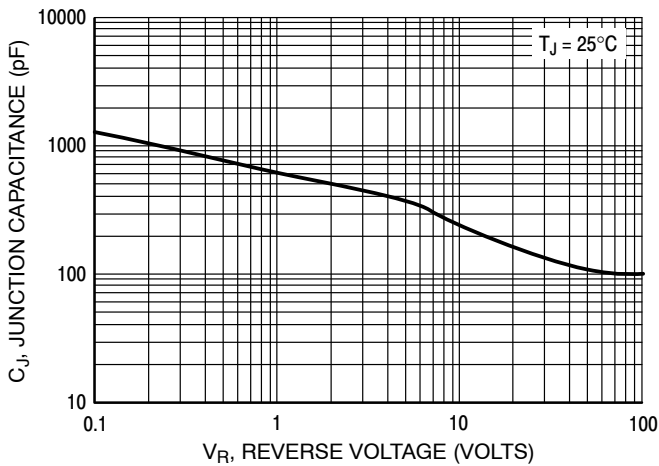


Figure 3. Typical Junction Capacitance

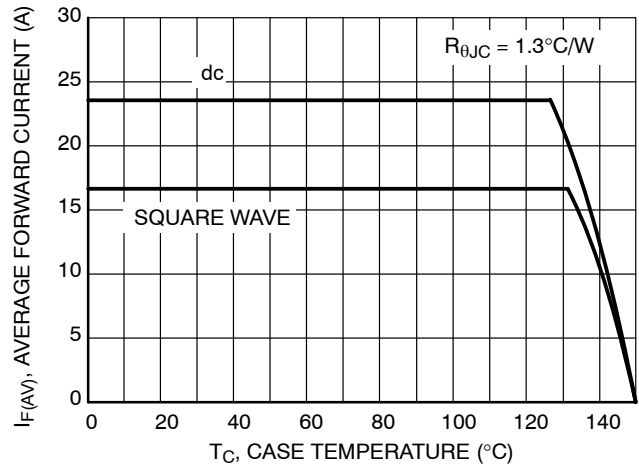


Figure 4. Current Derating per Leg

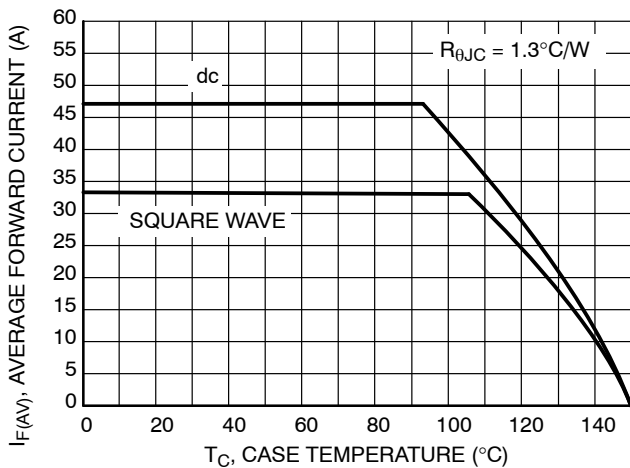


Figure 5. Current Derating

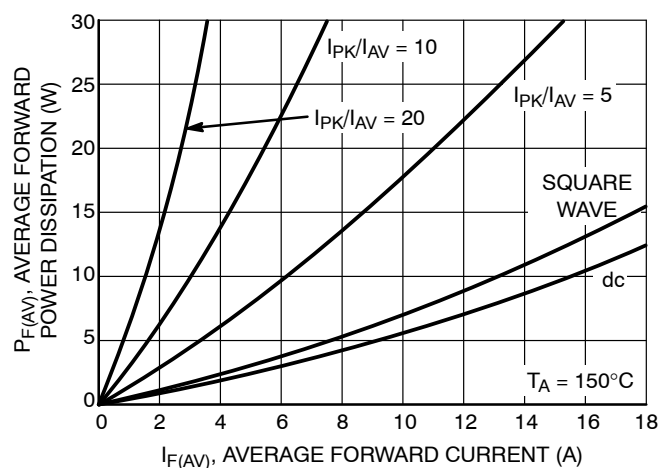


Figure 6. Forward Power Dissipation

TYPICAL CHARACTERISTICS

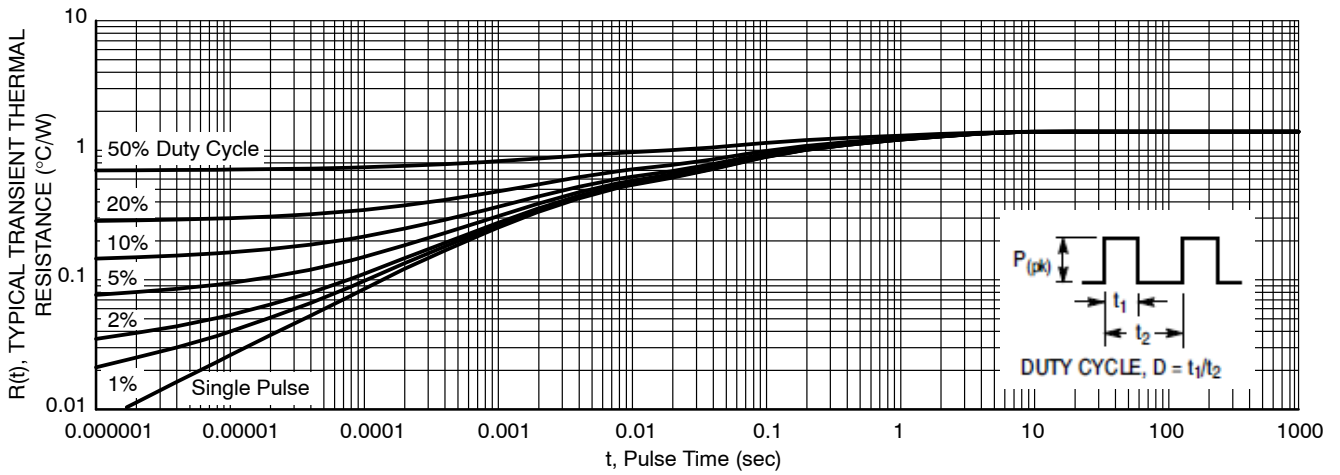


Figure 7. Typical Transient Thermal Response, Junction-to-Case for NTST30100CT and NTSB30100CT-1G

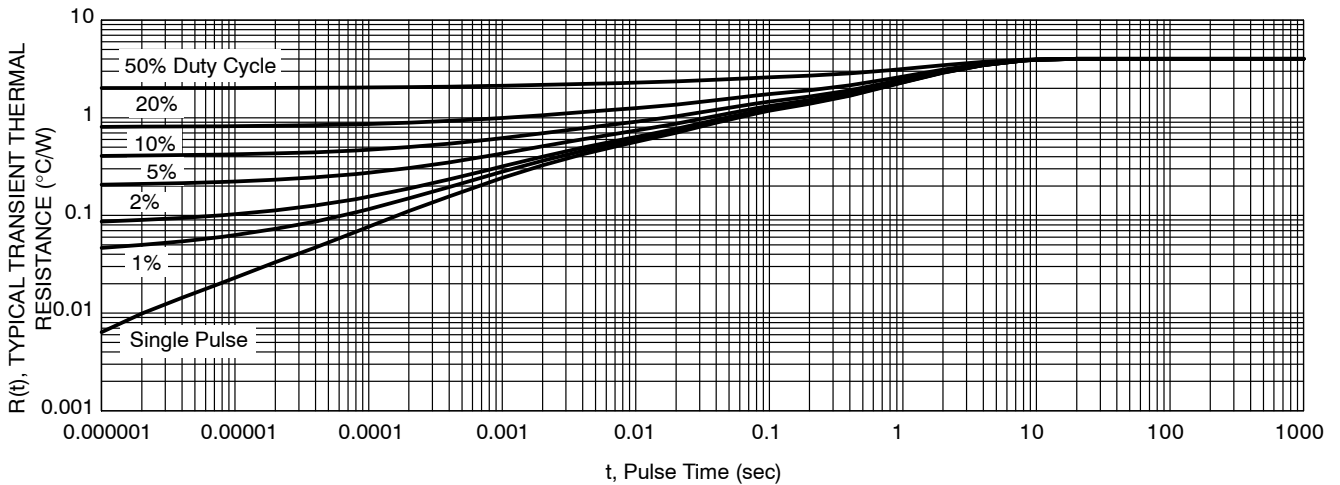


Figure 8. Typical Transient Thermal Response, Junction-to-Case for NTSJ30100CTG

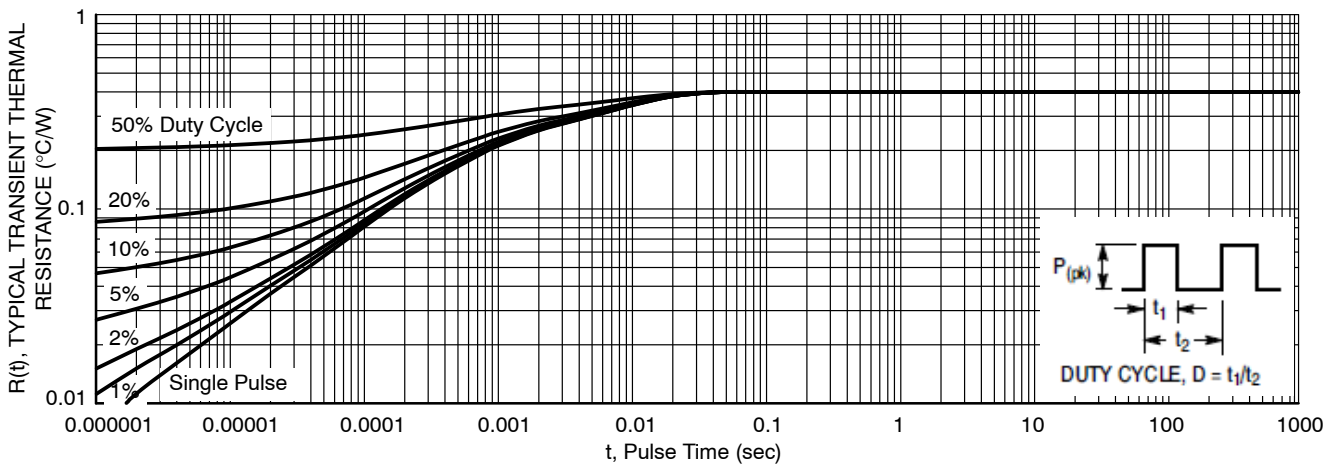


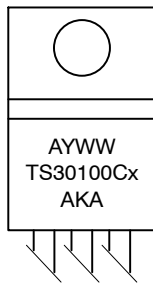
Figure 9. Typical Transient Thermal Response, Junction-to-Case for NTSB30100CTG

NTST30100CT, NTSB30100CT-1G, NTSJ30100CTG, NTSB30100CTG

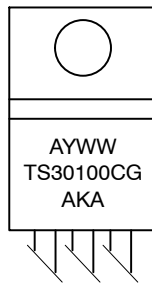
ORDERING INFORMATION

| Device | Package | Shipping |
|----------------|---------------------------------|-------------------|
| NTST30100CTG | TO-220AB (Pb-Free) | 50 Units / Rail |
| NTSB30100CT-1G | I ² PAK (Pb-Free) | 50 Units / Rail |
| NTSJ30100CTG | TO-220FP (Halide-Free) | 50 Units / Rail |
| NTSB30100CTG | D ² PAK (Pb-Free) | 50 Units / Rail |
| NTSB30100CTT4G | D ² PAK (Pb-Free) | 800 / Tape & Reel |

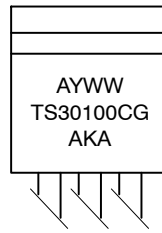
MARKING DIAGRAMS



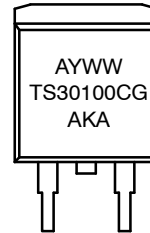
TO-220AB



TO-220FP



I²PAK



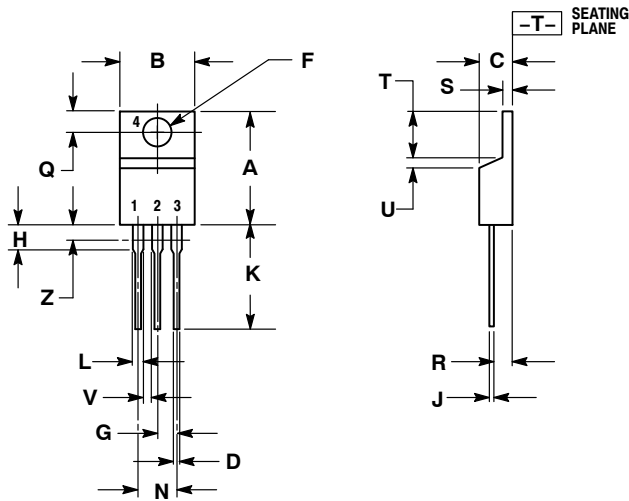
D²PAK

- A = Assembly Location
- Y = Year
- WW = Work Week
- AKA = Polarity Designator
- x = G or H
- G = Pb-Free Package
- H = Halide-Free Package

NTST30100CT, NTSTB30100CT-1G, NTSJ30100CTG, NTSTB30100CTG

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 ISSUE AF

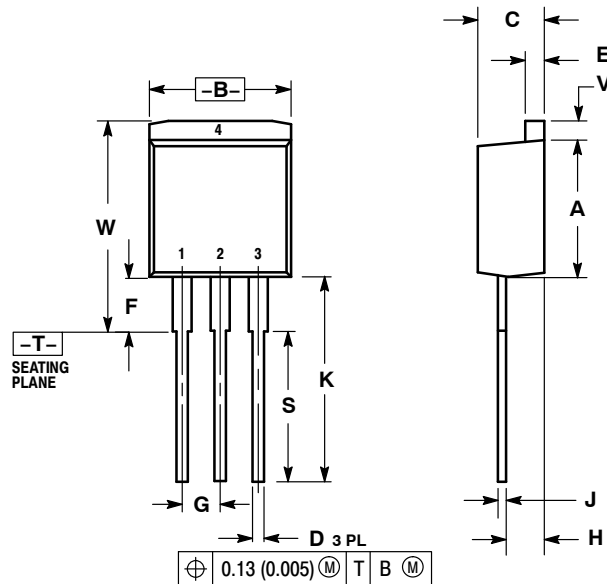


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.405 | 9.66 | 10.28 |
| C | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.161 | 3.61 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.014 | 0.025 | 0.36 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

- STYLE 6:
1. ANODE
 2. CATHODE
 3. ANODE
 4. CATHODE

I²PAK (TO-262) CASE 418D ISSUE D

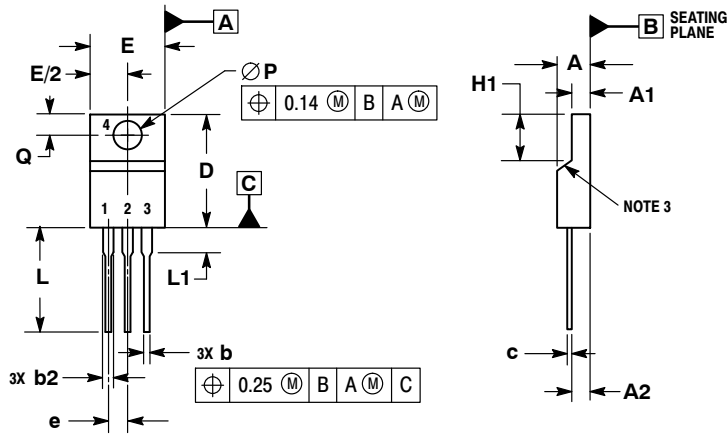


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.335 | 0.380 | 8.51 | 9.65 |
| B | 0.380 | 0.406 | 9.65 | 10.31 |
| C | 0.160 | 0.185 | 4.06 | 4.70 |
| D | 0.026 | 0.035 | 0.66 | 0.89 |
| E | 0.045 | 0.055 | 1.14 | 1.40 |
| F | 0.122 REF | | 3.10 REF | |
| G | 0.100 BSC | | 2.54 BSC | |
| H | 0.094 | 0.110 | 2.39 | 2.79 |
| J | 0.013 | 0.025 | 0.33 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| S | 0.390 REF | | 9.90 REF | |
| V | 0.045 | 0.070 | 1.14 | 1.78 |
| W | 0.522 | 0.551 | 13.25 | 14.00 |

PACKAGE DIMENSIONS

TO-220 FULLPACK, 3-LEAD
CASE 221AH
ISSUE B



NOTES:

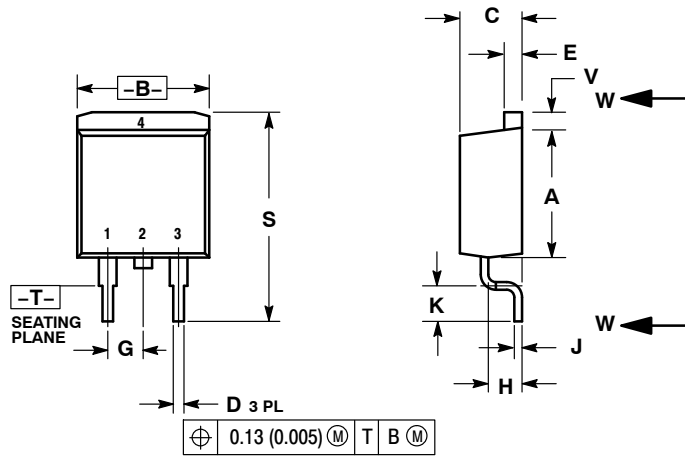
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.

| DIM | MILLIMETERS | |
|-----|-------------|-------|
| | MIN | MAX |
| A | 4.30 | 4.70 |
| A1 | 2.50 | 2.90 |
| A2 | 2.50 | 2.70 |
| b | 0.54 | 0.84 |
| b2 | 1.10 | 1.40 |
| c | 0.49 | 0.79 |
| D | 14.70 | 15.30 |
| E | 9.70 | 10.30 |
| e | 2.54 BSC | |
| H1 | 6.70 | 7.10 |
| L | 12.70 | 14.73 |
| L1 | --- | 2.80 |
| P | 3.00 | 3.40 |
| Q | 2.80 | 3.20 |

NTST30100CT, NTSB30100CT-1G, NTSJ30100CTG, NTSB30100CTG

PACKAGE DIMENSIONS

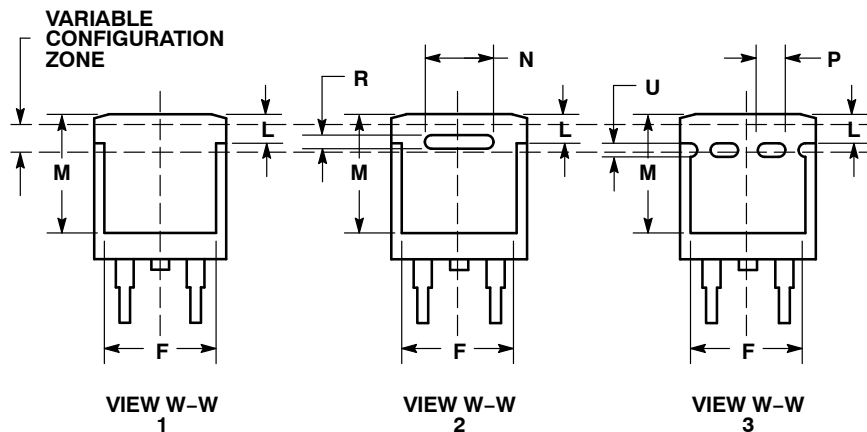
D²PAK 3 CASE 418B-04 ISSUE K



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.340 | 0.380 | 8.64 | 9.65 |
| B | 0.380 | 0.405 | 9.65 | 10.29 |
| C | 0.160 | 0.190 | 4.06 | 4.83 |
| D | 0.020 | 0.035 | 0.51 | 0.89 |
| E | 0.045 | 0.055 | 1.14 | 1.40 |
| F | 0.310 | 0.350 | 7.87 | 8.89 |
| G | 0.100 BSC | | 2.54 BSC | |
| H | 0.080 | 0.110 | 2.03 | 2.79 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| K | 0.090 | 0.110 | 2.29 | 2.79 |
| L | 0.052 | 0.072 | 1.32 | 1.83 |
| M | 0.280 | 0.320 | 7.11 | 8.13 |
| N | 0.197 REF | | 5.00 REF | |
| P | 0.079 REF | | 2.00 REF | |
| R | 0.039 REF | | 0.99 REF | |
| S | 0.575 | 0.625 | 14.60 | 15.88 |
| V | 0.045 | 0.055 | 1.14 | 1.40 |



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JONHON

«JONHON» (основан в 1970 г.)

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«FORSTAR» (основан в 1998 г.)

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Телефон: 8 (812) 309-75-97 (многоканальный)

Факс: 8 (812) 320-03-32

Электронная почта: ocean@oceanchips.ru

Web: <http://oceanchips.ru/>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, д. 2, корп. 4, лит. А